

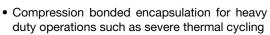
# Phase Control Thyristors (Stud Version), 110 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	110 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 800 V, 1200 V, 1600 V			
V <sub>TM</sub>	1.52 V			
I <sub>GT</sub>	150 mA			
T <sub>J</sub>	-40 °C to +125 °C			
Package	TO-94 (TO-209AC)			
Circuit configuration	Single SCR			

#### **FEATURES**

- · Center gate
- International standard case TO-94 (TO-209AC)





- ROHS
- Hermetic glass-metal case with ceramic insulator (Glass-metal seal over 1200 V)
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912">www.vishav.com/doc?99912</a>

#### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		110	Α		
I <sub>T(AV)</sub>	T <sub>C</sub>	90	°C		
I <sub>T(RMS)</sub>		175			
I <sub>TSM</sub>	50 Hz	2700	А		
	60 Hz	2830			
I <sup>2</sup> t	50 Hz	36.4	kA <sup>2</sup> s		
1-1	60 Hz	33.2	KA-5		
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 1600	V		
tq	Typical	100	μs		
TJ		-40 to +125	°C		

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$\begin{split} I_{DRM}/I_{RRM} & \text{MAXIMUM AT} \\ T_J &= T_J & \text{MAXIMUM} \\ & \text{mA} \end{split}$			
	04	400	500				
VS-ST110S	08	800	900	20			
V5-511105	12	1200	1300	20			
	16	1600	1700				



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current at case temperature	I <sub>T(AV)</sub>	180° conduction, half sine wave		110 90	A °C	
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 85 °C	case temperat	ure	175	
	,	t = 10 ms	No voltage		2700	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		2830	А
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	Sinusoidal half wave,	2270	
		t = 8.3 ms	reapplied		2380	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	36.4	kA <sup>2</sup> s
	l <sup>2</sup> t	t = 8.3  ms	reapplied		33.2	
		t = 10 ms	100 % V <sub>RRM</sub>		25.8	
		t = 8.3  ms	reapplied		23.5	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10	) ms, no voltage	e reapplied	364	kA <sup>2</sup> √s
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % x π	$x \ I_{T(AV)} < I < \pi \ x$	$I_{T(AV)}$ , $T_J = T_J$ maximum	0.90	V
High level value of threshold voltage	$V_{T(TO)2}$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		0.92	٧	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		1.79	mΩ	
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum} $ 1.81		1.81	11122	
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 350 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$ 1.52		V		
Maximum holding current	I <sub>H</sub>	T _ 25 °C	anada ayanlı 1	2 V registive lead	600	mA
Typical latching current	ΙL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load		1000	IIIA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	500	A/μs	
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}$ , $T_J = 25 °C$	2.0		
Typical turn-off time	t <sub>q</sub>	$I_{TM}$ = 100 A, $T_J$ = $T_J$ maximum, $dI/dt$ = 10 A/ $\mu$ s, $V_R$ = 50 V, $dV/dt$ = 20 V/ $\mu$ s, gate 0 V 100 $\Omega$ , $t_p$ = 500 $\mu$ s	100	μs	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub>	500	V/µs	
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	20	mA	



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		
PARAMETER	STWIBUL	l Es	ST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	,	5	W
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50		1	VV
Maximum peak positive gate current	I <sub>GM</sub>			2	.0	Α
Maximum peak positive gate voltage	+ V <sub>GM</sub>	$T_J = T_J$ maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms		<u>:</u> 0	V
Maximum peak negative gate voltage	- V <sub>GM</sub>				5.0	
		T <sub>J</sub> = -40 °C		180	-	
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Maximum required gate trigger/ current/voltage are the lowest	90	150	mA
		T <sub>J</sub> = 125 °C		40	-	
		T <sub>J</sub> = -40 °C	value which will trigger all units	2.9	-	
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	6 V anode to cathode applied	1.8	3.0	V
		T <sub>J</sub> = 125 °C		1.2	-	
DC gate current not to trigger	$I_{GD}$		Maximum gate current/voltage	10		mA
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J \text{ maximum}$	not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	TJ		-40 to 125	°C	
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150		
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	R <sub>thJC</sub> DC operation 0.		K/W	
Maximum thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased	0.08	rv vv	
Mounting torque, ± 10 %		Non-lubricated threads 15.5 (137)		Nm	
Wounting torque, ± 10 %		Lubricated threads	14 (120)	(lbf $\cdot$ in)	
Approximate weight			130	g	
Case style		See dimensions - link at the end of datasheet	TO-94 (T	O-209AC)	

△R <sub>thJC</sub> CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS		
180°	0.035	0.025				
120°	0.041	0.042				
90°	0.052	0.056	$T_J = T_J$ maximum	K/W		
60°	0.076	0.079				
30°	0.126	0.127				

#### Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

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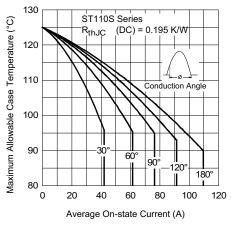


Fig. 1 - Current Ratings Characteristics

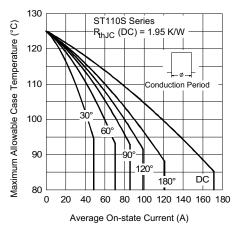


Fig. 2 - Current Ratings Characteristics

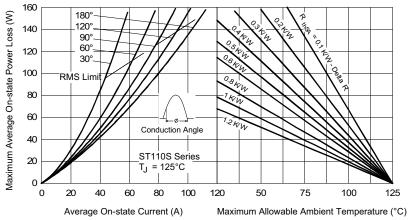


Fig. 3 - On-State Power Loss Characteristics

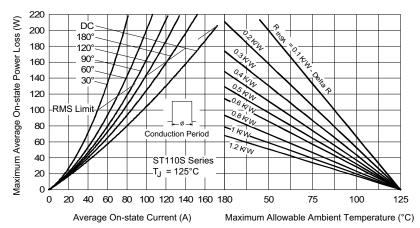


Fig. 4 - On-State Power Loss Characteristics



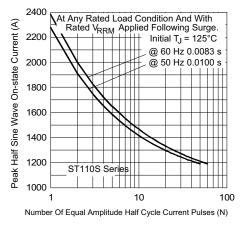


Fig. 5 - Maximum Non-Repetitive Surge Current

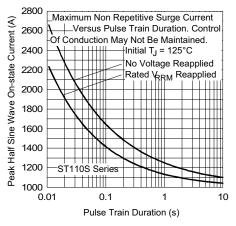


Fig. 6 - Maximum Non-Repetitive Surge Current

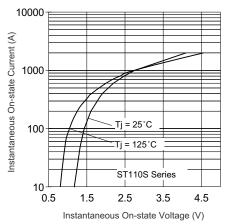


Fig. 7 - On-State Voltage Drop Characteristics

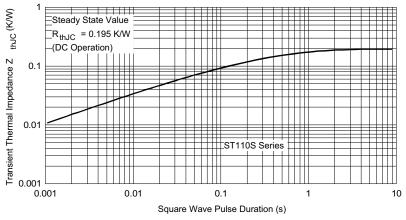


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristic

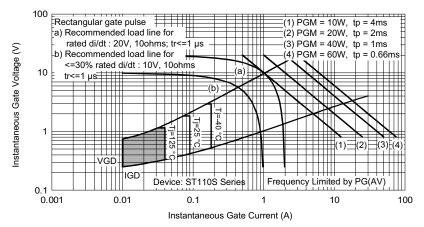
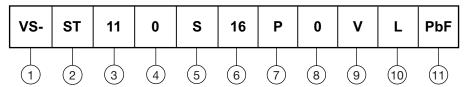


Fig. 9 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



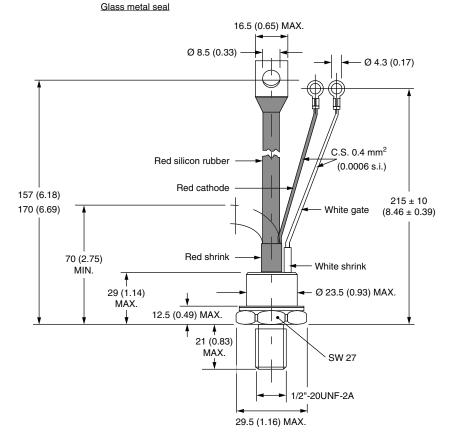
- Vishay Semiconductors product
- **Thyristor**
- Essential part marking
- 0 = converter grade
- S = compression bonding stud
- 3 4 5 6 Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)
- P = stud base 20UNF threads
- 0 = eyelet terminals (gate and auxiliary cathode leads)
  - 1 = fast-on terminals (gate and auxiliary cathode leads)
  - 2 = flag terminals (for cathode and gate terminals)
- 9 • V = glass-metal seal (only up to 1200 V)
  - None = ceramic housing (over 1200 V)
- 10 Critical dV/dt:
  - None = 500 V/µs (standard value)
  - L = 1000 V/µs (special selection)
- 11 None = standard production
  - PbF = lead (Pb)-free

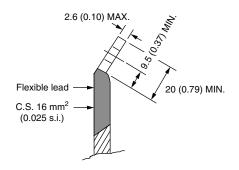
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95078

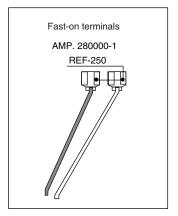


## TO-209AC (TO-94) for ST110S Series

#### **DIMENSIONS** in millimeters (inches)







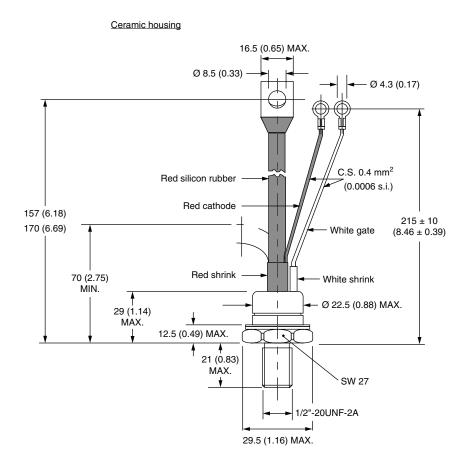
### **Outline Dimensions**

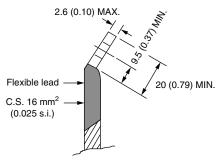
### Vishay Semiconductors

### TO-209AC (TO-94) for ST110S Series



#### **DIMENSIONS** in millimeters (inches)





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T2160N28TOF VT TT251N16KOF-K VS-22RIA100 VS-16RIA40 TD250N16KOF-A VS-ST110S16P0 T930N36TOF VT T2160N24TOF

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